

DESCRIPTION

The MS1006 is a 50 V Class AB epitaxial silicon NPN planar transistor designed primarily for SSB and VHF communications. This device utilizes emitter ballasting for improved ruggedness and reliability.

IMPORTANT: For the most current data, visit: <http://www.advancedpower.com>

KEY FEATURES

- Optimized for SSB
- 30 MHz
- 50 Volts
- Common Emitter
- Gold Metallization
- $P_{OUT} = 75$ W Min.
- $G_P = 14$ dB Gain

APPLICATIONS/BENEFITS

- HF SSB Applications

ABSOLUTE MAXIMUM RATINGS ($T_{CASE} = 25^{\circ}C$)

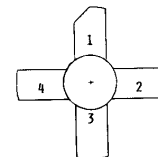
Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	110	V
V_{CEO}	Collector-Emitter Voltage	55	V
V_{EBO}	Emitter-Base Voltage	4.0	V
I_C	Device Current	3.25	A
P_{DISS}	Power Dissipation	127	W
T_J	Junction Temperature	+200	$^{\circ}C$
T_{STG}	Storage Temperature	-65 to +150	$^{\circ}C$



.380 4LSTUD(M135)
epoxy sealed

THERMAL DATA

$R_{TH(j-c)}$	Junction-Case Thermal Resistance	2.0	$^{\circ}C/W$
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PIN CONNECTION


1 collector 3 base
2 emitter 4 emitter

STATIC ELECTRICAL SPECIFICATIONS (TCASE = 25°C)

Symbol	Test Conditions	MS1006			Units
		Min.	Typ.	Max.	
BV_{CES}	I_C = 100 mA V_{BE} = 0 V	110	—	—	V
BV_{CEO}	I_C = 200 mA I_B = 0 mA	55	—	—	V
BV_{EBO}	I_E = 10 mA I_C = 0 mA	4.0	—	—	V
h_{FE}	V_{CE} = 6 V I_C = 1.4 A	19	—	50	—

DYNAMIC ELECTRICAL SPECIFICATIONS (TCASE = 25°C)

Symbol	Test Conditions	MS1006			Units
		Min.	Typ.	Max.	
P_{OUT}	f = 30 MHz V_{CE} = 50 V	75	—	—	W
G_p*	P_{OUT} = 75 W PEP V_{CE} = 50 V	14	—	—	dB
IMD*	P_{OUT} = 75 W PEP V_{CE} = 50 V	—	—	-30	dBc
η_C*	P_{OUT} = 75 W PEP V_{CE} = 50 V	37	—	—	%
C_{OB}	f = 1 MHz V_{CB} = 50 V	—	—	100	PF

Note: *f₁ = 30.00 MHz, f₂ = 30.01 MHz

